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電源管理



顯示驅動



二三極管



LDO穩壓器



觸摸芯片



MOS管



運算放大器



存儲芯片



MCU



串口通信

MMBTA44 3D

產品規格說明書

MMBTA44 3D NPN Plastic-Encapsulate Transistors

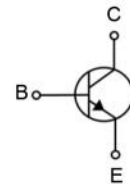
Features

- Collector Current: $I_C=0.2A$
- Power Dissipation of 350mw

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MMBTA44	SOT-23	3D	3000

SOT-23



Maxmim Ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V_{CBO}	350	V
Collector-Emitter Voltage	V_{CEO}	350	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	200	mA
Collector Power Dissipation	P_C	350	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	357	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55~+150	°C

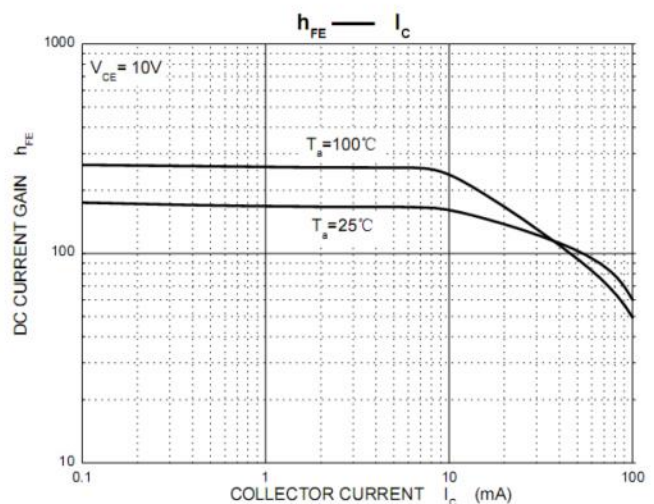
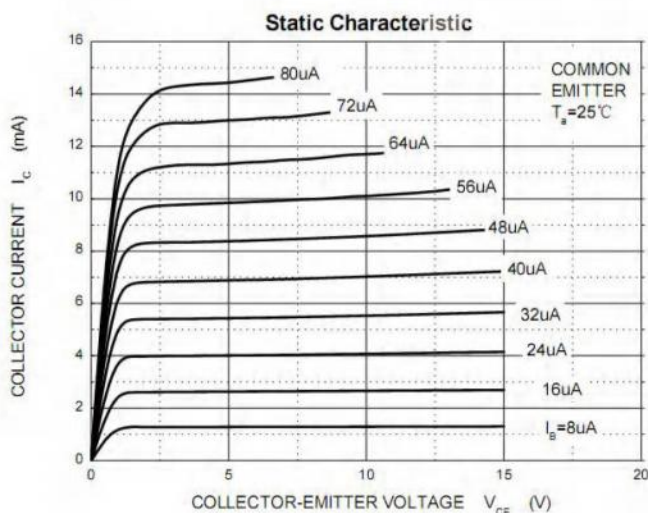
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Electrical Characteristics ($T_a=25^\circ\text{C}$ unless otherwise specified)

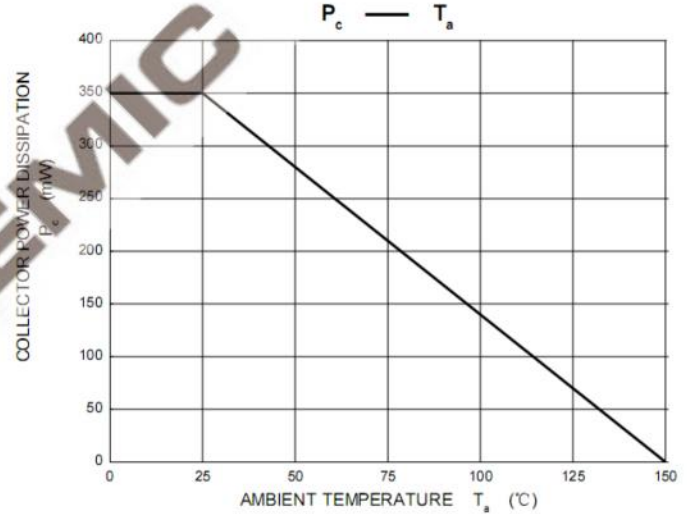
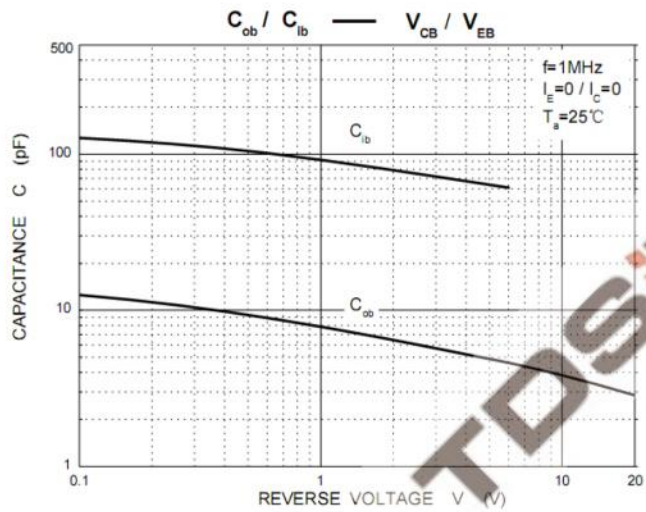
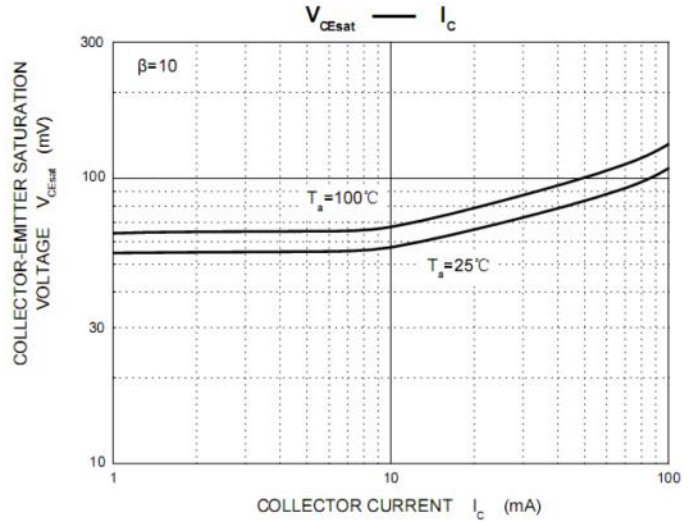
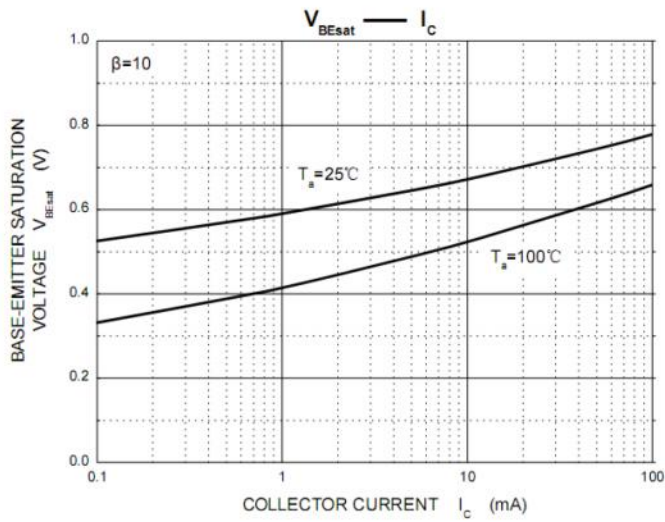
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}$, $I_E=0$	350			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}^*$	$I_C=1\text{mA}$, $I_B=0$	350			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}$, $I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=300\text{V}$, $I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4\text{V}$, $I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}^*$	$V_{CE}=10\text{V}$, $I_C=1\text{mA}$	40			
	$h_{FE(2)}^*$	$V_{CE}=10\text{V}$, $I_C=10\text{mA}$	50		200	
	$h_{FE(3)}^*$	$V_{CE}=10\text{V}$, $I_C=50\text{mA}$	45			
	$h_{FE(4)}^*$	$V_{CE}=10\text{V}$, $I_C=100\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)1}^*$	$I_C=1\text{mA}$, $I_B=0.1\text{mA}$			0.4	V
	$V_{CE(sat)2}^*$	$I_C=10\text{mA}$, $I_B=1\text{mA}$			0.5	V
	$V_{CE(sat)3}^*$	$I_C=50\text{mA}$, $I_B=5\text{mA}$			0.75	V
Base-emitter saturation voltage	$V_{BE(sat)}^*$	$I_C=10\text{mA}$, $I_B=1\text{mA}$			0.75	V
Collector output capacitance	C_{ob}	$V_{CB}=20\text{V}$, $I_E=0$, $f=1\text{MHz}$			7	pF
Emitter input capacitance	C_{ib}	$V_{EB}=0.5\text{V}$, $I_C=0$, $f=1\text{MHz}$			130	pF
Transition frequency	f_T	$V_{CE}=20\text{V}$, $I_C=10\text{mA}$, $f=30\text{MHz}$	50			MHz

*Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycles $\leq 2.0\%$.

Typical Characteristics

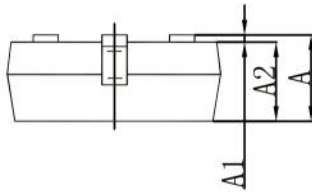
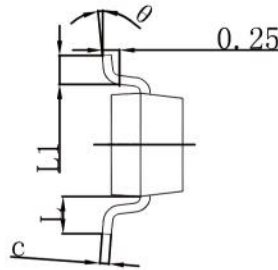
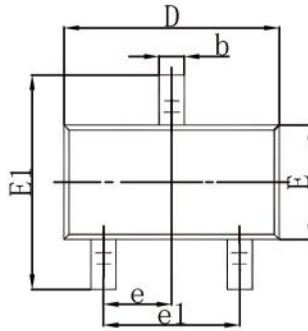


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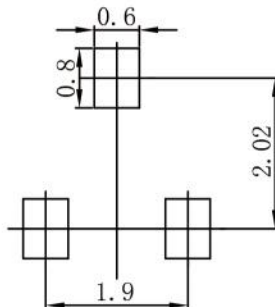
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SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
theta	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.